Mic Mc

SINGLE PHASE GLASS PASSIVATED BRIDGE RECTIFIER

MB05S - MB10S

50 TO 1000V

Features

Surface Mount Package Glass passivated Diode Construction Moisture Resistant Epoxy Case High Surge Current Capability

Maximum Ratings

Operating Temperature:-55^oC to +150^oC Storage Temperature:-55^oC to +150^oC

MCC Catalog Number	Device Marking	Maximum Rccurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MB05S	MB05S	50V	35V	50V
MB1S	MB1S	100V	70V	100V
MB2S	MB2S	200V	140V	200V
MB4S	MB4S	400V	280V	400V
MB6S	MB6S	600V	420V	600V
MB8S	MB8S	800V	560V	800V
MB10S	MB10S	1000V	700V	1000V

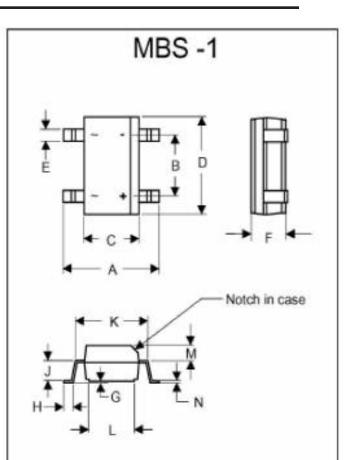
Electrical Characteristics @ 25⁰C Unless Otherwise Specifie

Average Forward Current	I _{F(AV)}	0.5A 0.8A	Note1 $T_A = 40^{\circ}C$ Note2 $T_A = 40^{\circ}C$
Peak Forward Surge Current	I _{FSM}	30A	8.3ms, half sine
Maximum Instantaneous Forward Voltage	V _F	1.0V	I _{FM} =0.5A; T _A =25 ^o C
Maximum DC Reverse Current At Rated DC BlockingVoltage	I _R	5uA	T _A =25 ⁰ C
Typical Junction Capacitance	CJ	25pF	Measured at1.0MHz, V _R =4.0V

Note1. Measured at 1.0 MHz and applied reverse voltage of 4.0 volts Note2. On alum: substrate P.C.B with an rea of 0.8 * 0.8 * 0.25

(20 * 20 * 6.4mm) mounte on 0.05 * 0.05 "(13 * 13 mm) solder pad.

*Pulse Test: Pulse Width 300usec, Duty Cycle 1%



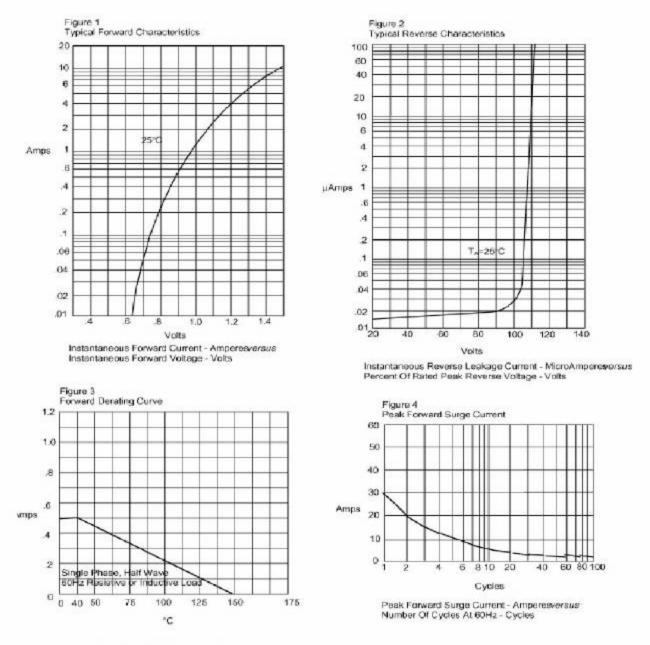
DIM	INC HES		MM		
	MIN	MAX	MIN	MAX	NOTE
A	.252	.272	6.40	6.91	
B	.095	.105	2.41	2.67	
C	1.45	.155	3.68	3.94	
D	.180	.190	4.57	4.83	
E	.017	.029	0.45	0.75	
F	.090	.106	2.30	2.70	
G	.004	008	0.10	0.20	1
н	.021	.023	0.53	0.58	
3	055	.065	1.40	1.65	
ĸ		.200	-	5.08	
L	.107	.117	2.72	2.97	
M	040	.050	1.02	1.27	
D	.008	.014	0.15	0.35	

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Average Forward Rectified Current - Amperesversus Ambient Temperature -°C